Diode Semiconductor Device - Page 1 of 1



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Inclosure Materia	al:
Metal	
Overall Length:	
Between 0.300 inc	ches and 0.405 inches
Overall Diameter	:
Between 0.255 inc	ches and 0.424 inches
Mounting Facility	y Quantity:
1	
Electrode Interna	ally-electrically Connected To Case:
Cathode	
Mounting Method	d:
Threaded stud	
Features Provide	ed:
Hermetically seale	ed case
Thread Size:	
0.190 inches	
Semiconductor M	Aaterial:
Silicon	
Voltage Rating In	n Volts Per Characteristic:
62.0 regulator vo	ltage
Current Rating P	er Characteristic:
40.00 milliampere	s repetitive peak forward current
Power Rating Per	r Characteristic:
10.0 watts small-s	signal input power, common-collector preset
Maximum Operat	ting Tempurature Per Measurement Point:
175.0 degrees cel	sius case
Test Data Docum	ient:
81349-mil-s-1950(0 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification
format; excludes	commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain
environmental and	d performance requirements and test conditions that are shown as "typical", "average", "", etc.).
Thread Series De	esignator:
Unf	
Terminal Type Ar	nd Quantity:
1 tab, solder lug a	and 1 threaded stud
Specification Dat	ta:
81349-mil-s-1950(0/124 government specification
Shelf Life:	
N/a	
Unit Of Measure:	
 Demilitarization:	
No	
Fiig:	
A110a0	